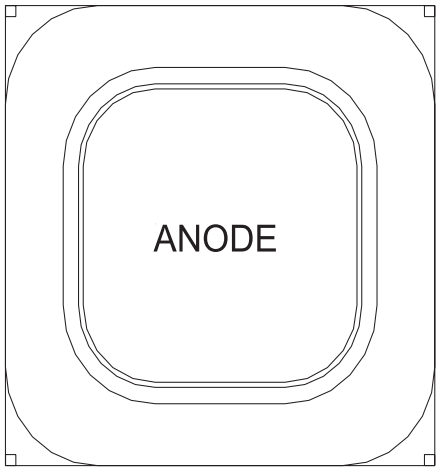
Central™
Semiconductor Corp.

PROCESS CPD48V
Schottky Diode
High Current Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 x 14 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



R1

BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

62,250

PRINCIPAL DEVICE TYPES

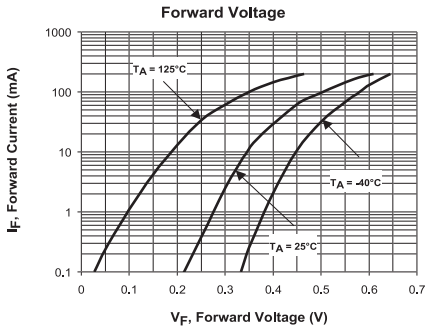
CMPSH-3 Series
CMSSH-3 Series
CMXSH-3
CMKSH-3T

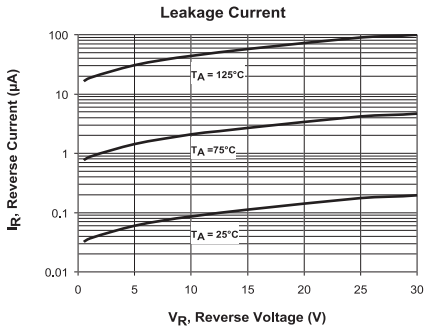
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

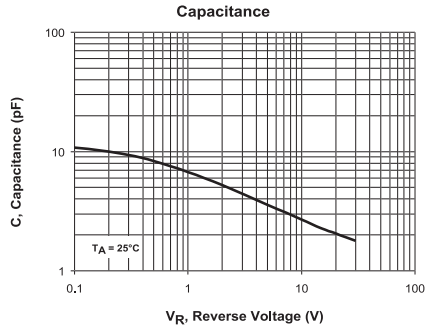
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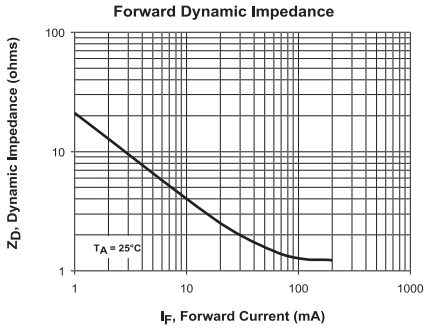
Central Semiconductor Corp.

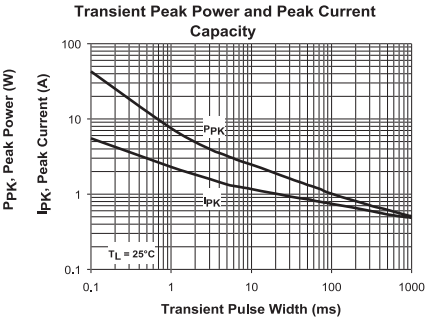
PROCESS CPD48V
Typical Electrical Characteristics

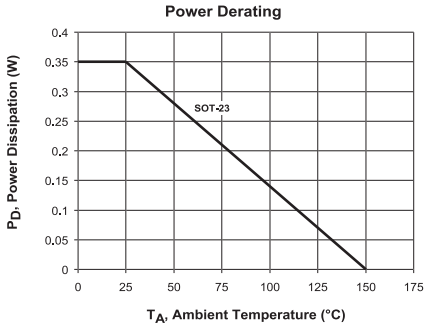












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